



4~10 Series Cell Battery Monitor and Protection IC

DESCRIPTION

JW3370 is a multi-cell battery stack monitoring and protection IC that includes a 14-bit ADC for battery voltage and temperature sense, a 16-bit ADC for charge/discharge current sense.

JW3370 provides passive balance function for each cell and allows at most 3 consecutive cells being discharged simultaneously.

JW3370 communicates with external control unit via SPI interface. More JW3370 can operate in series to monitor long string battery.

JW3370 integrates complete protection function including over/under voltage, over/under temperature, over charge/discharge current, short-circuit and open wire detection. When fault(s) happen, JW3370 will send alarm signal to inform host and shutdown CHG or DSG.

JW3370 integrated pre-charge and pre-discharge drivers for the deep discharge battery or some big capacitor load startup.

JW3370 supports both Sleep mode and Ship mode to achieve high efficiency with low power when charge/discharge current is minor.

Company's Logo is Protected, "JW" and "JOULWATT" are Registered
Trademarks of Joulwatt Technology Co., Ltd.

FEATURES

- Monitor 10 Series Cell Battery and Support Series Operation
- 14-bit ΔΣ ADC Samples Battery Voltage and Accuracy is ±5mV Typ. @2.3~4.3V
- Provide Filtering 3 Channels Thermal Sense and Accuracy is ±1°C (No Considering NTC Resistor Offset)
- Battery Over/Under Voltage Protection
- Battery Over/Under Temperature Protection
- Open Wire Connection Detection
- 10 Cells Passive Balance
 On-Chip Passive Cell Balancing Switches
 Provide Off-Chip Passive Balancing
- 16-bit ΔΣ ADC Senses Charge/Discharge Current and Accuracy is ±75μV Typ.@(-100 mV ~100mV)
 ±150μV Typ.@(-190 mV ~190mV)
- Over Charge/Discharge Current Protection
- Discharge Short-Circuit Protection
- Reliable SPI Communication (Mode3)
- 3.3V LDO Output for External Application
- External Protection N-MOSFETs
- Integrated Pre-charge/discharge Function
- Low Power Consumption

During Operation 1.5mA typ. 1.8mA Max (Power Consumption of Communication and Temperature Detection is not Included)

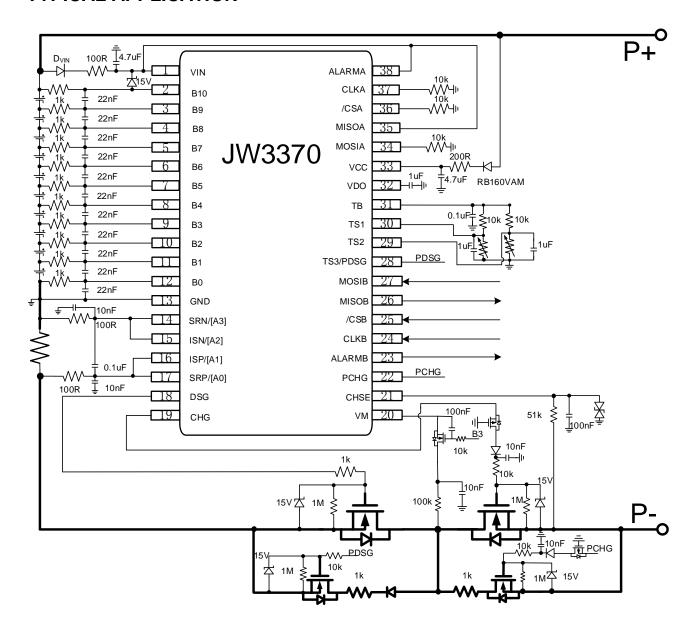
During Sleep 18μA typ. 20μA Max During Ship 3.2μA typ. 5μA Max

Package: TSSOP38

APPLICATIONS

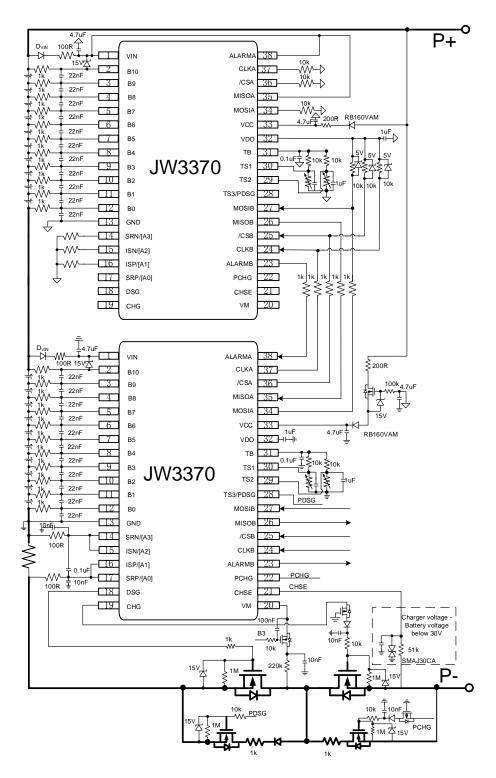
- Electric Bicycles, Motorcycles.
- Backup Battery Systems
- Hybrid Electric Vehicle

TYPICAL APPLICATION



10 Cells Low Side Driver

Note: D_{VIN} recommends using Schottky diode, witch the forward voltage (V_F) is less than 0.3V.



20 Cells Low Side Driver

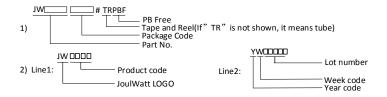
Note: When the charger voltage is 30V higher than the battery voltage, there will be leakage current during charging.

$$I_{Leakage}(A) = \frac{V_{charger}(V) - V_{BAT}(V) - V_{TVS}(V)}{51k\Omega}$$

ORDER INFORMATION

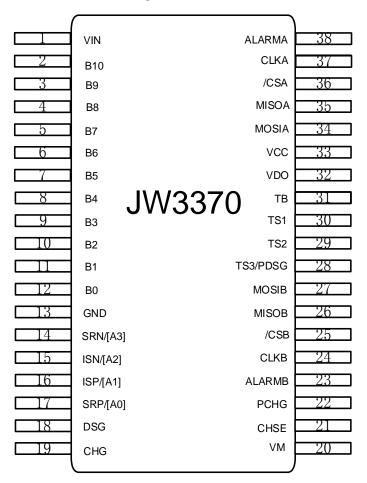
DEVICE ¹⁾	PACKAGE	TOP MARKING ²⁾
IVA/2270TCCODE#TDDDE	TCCOD20	JW3370
JW3370TSSOPF#TRPBF	TSSOP38	YW□□□□□

Notes:



PIN CONFIGURATION

TOP VIEW



TSSOP38

ABSOLUTE MAXIMUM RATING¹⁾

VIN-GND, VCC-GND	0.	3V to 60V
B(N)-GND N=04	0.	3V to 40V
B(N)-GND N=510	0.	3V to 60V
B(N)-B(N-1) N=110	0.	3V to 20V
B10-VIN	20	V to 0.6V
SRP		5V to 40V
CHSE	GND-4	0V to 60V
VM, CHG	0.	3V to 60V
DSG		
/CSB, CLKB, MOSIB	<u>[</u>	5V to 6.5V
MOSIA, /CSA, CLKA, MISOA, ALARMA		
All Other Pins	0.3	3V to 6.5V
Junction Temperature ²⁾		150°C
Lead Temperature		260°C
Storage Temperature		
RECOMMENDED OPERATING CONDITIONS ³⁾		
B(N)-B(N-1) N=110		0V to 5V
VIN-GND		
Operating Junction Temperature	40°C	to +85°C
THERMAL PERFORMANCE ⁴⁾	0	0
	$ heta_{J\!A}$	
TSSOP38	86	19°C/W

Note:

- 1) Exceeding these ratings may damage the device. These stress ratings do not imply function operation of the device at any other conditions beyond those indicated under RECOMMEND OPERATION CONDITIONS.
- 2) The JW3370includes thermal protection that is intended to protect the device in overload conditions. Continuous operation over the specified absolute maximum operating junction temperature may damage the device.
- 3) The device is not guaranteed to function outside of its operating conditions.
- 4) Measured on JESD51-7, 4-layer PCB.

ELECTRICAL CHARATERISTICS

ITEM	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNITS
Power Supply						
Operation voltage on VIN	VIN		8		50	V
Startup voltage of VIN and VCC	V _{IN_START}			5.5	6	V
On anti-manage of MN and		T _A =-40°C ⁵⁾	1.2	1.45	1.8	mA
Operation current of VIN and VCC	I _{IN_O}	T _A =25℃	1.3	1.5	1.8	mA
VCC		T _A =85 °C ⁵⁾	1.4	1.64	1.9	mA
		T _A =-40°C ⁵⁾	17	18	20	μΑ
Sleep current of VIN and VCC	I _{IN_L}	T _A =25°C	17	18	20	μΑ
		T _A =85 °C ⁵⁾	19	20	24	μΑ
		T _A =-40°C ⁵⁾	2.3	2.6	4	μΑ
Ship current of VIN	l _{IN_} s	T _A =25℃	2.4	3.2	5	μΑ
		T _A =85 °C ⁵⁾	3.4	3.8	6	μΑ
1.00	V _{DO}	No Load	3.2	3.3	3.4	V
LDO output voltage		I _{LOAD} =50mA	3.2	3.3	3.4	V
TI 11: 14 (0.0)()	.,	No Load	3.26	3.3	3.31	V
Thermal bias voltage (3.3V)	V _{ТВ}	I _{LOAD} =2mA	3.26	3.3	3.31	V
LDO output current limit	I _{LMT_LDO}		70	100		mA
LDO turn off delay time	tLDO_OFF ⁵⁾			1		s
TB output current limit	І _{LМТ_ТВ}			12		mA
LDO/TB over thermal warning threshold	T _{LDO_WAR} 5)		115	125	135	°C
LDO/TB over thermal protection threshold	T _{LDO_PRO} 5)		138	150	162	°C
Thermal shutdown threshold	T _{SHUTD} ⁵⁾			150		°C
Thermal hysteresis	T _{HYS} 5)			25		°C
14-BIT ADC (for cell voltage and	d temperature n	nonitor)				
Resolution of ADC	V _{VREV} 5)			0.305		mV
Measurement range of ADC	V _{RANGEV} ⁵⁾		0		5.0	V
Offset voltage of measurement	Voffsetv ⁵⁾		-0.5	0	0.5	mV
Error voltage of measurement	V _{ERR}	V _{CELL} =2.3V~4.3V T _A =25°C	-7	5	7	mV

		_				
		$V_{CELL}=2.3V-4.3V$ $T_{A}=-20^{\circ}C$ $\sim 65^{\circ}C^{5)}$	-15		15	mV
		V _{CELL} =2.3V~4.3V T _A = - 40°C ~85°C ⁵)	-20		20	mV
		Normal mode T _A =25°C	0.9	1	1.1	MHz
Frequency of ADC clock	fclk	Normal mode $T_A= -40^{\circ}C$ $\sim 85^{\circ}C^{5)}$	0.85		1.15	MHz
		Fast mode,				
Manager time of single call	± 5)	Setting: Control		0.04		
Measure time of single cell	tunitv ⁵⁾	Parameter Set: bit		0.64		ms
		[49:48]=0x0				
		Fast mode,				
	_,	Setting: Control				
Measure time of 10 cells	tcycle ⁵⁾	Parameter Set: bit		6.4		ms
		[49:48]=0x0				
		Fast mode,				
Cell balancing relaxation time		Setting: Control				
before cell voltage measured	t _{CB_RELAX} 5)	Parameter Set: bit		0.64		ms
, and the second		[49:48]=0x0				
		Fast mode,				
Temperature measurement		Setting: Control				
interval	t _{TEMP} 5)	Parameter Set: bit		64		ms
		[49:48]=0x0				
16-BIT ADC (for current monito	r)					
Resolution of ADC	V _{VREC} 5)			6		μV
Measurement range of ADC	V _{RANGEC} 5)		-190		190	mV
ssouroment range of ADO	VIVAIGEO	Vsrp-srn =				
		- 100mV~100mV T _A =25°C	-150	±75	150	μV
Error voltage of measurement	V _{ERRC}	$V_{SRP-SRN} =$ - 190mV~190mV $T_{A}=25^{\circ}C$	-300	±150	300	μV
	LINO	$V_{SRP-SRN} =$ - 100mV~100mV $T_{A}=-20~65^{\circ}C^{5}$	-180		180	μV
		$V_{SRP-SRN} =$ - 190mV~190mV $T_{A}=-20~65^{\circ}C^{5}$	-360		360	μV

				$V_{SRP-SRN} =$ - 100mV~100mV $T_{A}=-40~85^{\circ}C^{5}$	-300		300	μV
				$V_{SRP-SRN} =$ - 190mV~190mV $T_{A}=-40~85^{\circ}C^{5)}$	-600		600	μV
Current measure t	ime cycle		t _{UNITC} 5)			132		ms
Protection								
Over charge/	Threshold Ran	ge	Voc/Vod		0		5	V
Over discharge	Step					19.53		mV
	Threshold Ran	ge	toc ⁵⁾		0.128		1.92	S
	Step					128		ms
Over charge	Threshold Ran	ge	toc ⁵⁾		0.512		7.68	S
delay time	Step					512		ms
	Accuracy				75%*toc- Step	toc	125%*t	
	Threshold Ran	ge	t _{OD} ⁵⁾		0.512		7.68	S
Over discharge	Step					512		ms
delay time	Threshold Ran	ge	t _{OD} ⁵⁾		1		15.36	S
•	Step					1024		ms
	Accuracy				75%*t _{OD} - Step	top	125%*t	
Temperature	Threshold Ran	ge	Vот		0		3.3	V
protection	Step					19.53		mV
	Threshold Ran	ge	t _{OT} ⁵⁾		0.512		7.68	S
Temperature	Step					512		ms
protection delay					75%*t _{ОТ} - Step	tот	125%*t от	
Disabassa	Threshold Ran	ge	V _{DOI1}		0		190	mV
Discharge over	Step					0.781		mV
current 1st Grade	Accuracy				-2		2	mV
Discharge over	Threshold Ran	ge	t _{DOI1} 5)		0.128		8.064	s
current 1st Grade	Step					256		ms
protection delay time	Accuracy				75%*t _{ODO}	t _{DOI1}	125%*t	
Discharge over	Threshold Ran	ge	V _{DOI2}		0		190	mV
current 2 nd	Step					0.781		mV

Grade	Accuracy		-2		2	mV
Discharge over	Threshold Rang	e	32		992	ms
current 2 nd	Step	t _{DOI2} 5)		32		ms
Grade protection	Threshold Rang	e	4		124	ms
delay time	Step	t _{DOI2} 5)		4		ms
	Threshold Rang	e	32		992	ms
Discharge over	Step	t _{DOI2} 5)		32		ms
current 2 nd	Threshold Rang	e	4		124	ms
Grade protection	Step	t _{DOI2} 5)		4		ms
delay time	Accuracy		75%*t _{ODO}	t _{DOI2}	125%*t	
Ob ant aireacit	Threshold Rang	e V _{SHT}	42.5		500	mV
Short circuit	Step			7.5		mV
protection	Accuracy		-10		10	%
	Threshold Rang	e t _{SHT} 5)	64		2048	μs
Short circuit	Step			64		μs
protection delay	Accuracy		75%*t _{SHT} -Step	tsнт	125%*t sht	
OI.	Threshold Rang	e V _{COI}	0		200	mV
Charge over	Step			0.781		mV
current	Accuracy		-2		2	mV
Charge over	Threshold Rang	e tcoi ⁵⁾	0.64		960	ms
current	Step			64		ms
protection delay time	Accuracy		75%*tcol- Step	tcoı	125%*t	
Open wire detec	tion current ⁵⁾		40	85	130	μA
Open wire detec	tion threshold ⁵⁾			200		mV
Balance						
R _{DSON} of balance	e switch	Rdson_bsw		50		Ω
Watchdog	Programmable	t _{WD} 5)	0.512		120	S
timer range for	Step			512		ms
balance	Accuracy		75%*t _{WD} - Step	t _{WD}	125%*t	
Balance over the threshold	ermal protection	T _{BALAN} 5)		150		ô
Balance over thermal protection hysteresis		TBALAN_HYST ⁵⁾		25		°C

Charge and Dis	scharge Drivers						
The high voltage	-	V _{DRIV}					
MOSFET driver	FET driver		CHG, DSG,	10	12	14	V
The high voltage	e of external	\/	DCHC BDSC	4.5	6	6.5	V
MOSFET driver		V _{PDRIV}	PCHG, PDSG	4.5	Ö	6.5	V
The sink current	of external	I _{SINK}	CHG	9	10		mA
MOSFET driver		ISINK	DSG	76	95		mA
The source curr	ent of external	Isource	CHG, DSG,	5	10		mA
MOSFET driver		ISOURCE	0110, 200,	, , , , , , , , , , , , , , , , , , ,	10		1101
The sink current	of Pre-charge and	I PD	PCHG, PDSG	4	5		mA
Pre-discharge			. 6116,1 266		Ů		
The source curr	ent of Pre-charge	Ірисна	PCHG	2.8	4		mA
The source curr	ent of	I _{PUDSG}	PDSG	2.8	5		mA
Pre-discharge							
Load State Det	ection and Charge		d Wakeup	1	I	T	
	oltage threshold	Vvм		0.7	1	1.6	V
	oull down resistor	Rvms			20		kΩ
Charger detection threshold	on voltage	V_{CHSE}		0.15	0.3	0.45	V
Charger detection	on pull up current	I _{CHSE}		0.5	1	1.7	μΑ
Charger detection falling edge deglitch time		t _{CHSE⁵⁾}				30	ms
1 0	Januar Thanashada		V	0.05	0.35	0.65	
Low Current Wa	ikeup inresnoia	V _{LC} Programmable	0.1	0.4	0.7	mV	
Low current wak	ceup time	t _{LC} ⁵⁾				30	ms
/CSB falling edg	e wake up deglitch	t/CSB ⁵⁾				30	ma
time		t/CSB ⁻⁷				30	ms
Input Current							
B10~B0 pin leal	kage current	ILK		-1.0	0	1.0	μΑ
ALARMB (exce	pt device address=	=1) Open Wire	and Interrupt Detect	ion			
ALARMB open	Cycle ⁵⁾				8		s
wire detection	High level time ⁵⁾				4		ms
	Cycle ⁵⁾				100		ms
ALARMB	High level time ⁵⁾		Interrupt off CHG	5		14	ms
interrupt	High level time ⁵⁾		Interrupt off DSG	15		25	ms
detection	High level time ⁵⁾		Interrupt off CHG and DSG	30		50	ms
			- I				

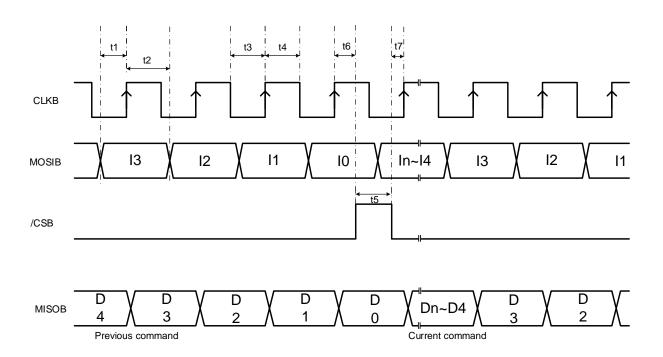
SPI Voltage Specifications								
Internal clock frequency at normal	,							
mode	fscLu			1		MHz		
Internal clock frequency at Sleep	t .			40		1.11-		
mode or idle mode	fscld			40		kHz		
Threshold of logic "L" of MOSIB,	V				0.0	V		
/CSB, CLKB	V_{ILB}				0.8	V		
Threshold of logic "H" of MOSIB,	V_{IHB}		2			V		
/CSB, CLKB	A IHR		2			V		
Output voltage of logic "L" of	Volb			0		V		
MISOB, ALARMB	VOLB			U		V		
Output voltage of logic "H" of	V_{OHB}			3.3		V		
MISOB, ALARMB	VORB			0.0		V		
Threshold of logic "L" of ALARMA,	VILA				VIN+0.	V		
MISOA	VILA				5	V		
Threshold of logic "H" of ALARMA,	Viha		VIN+2.2			V		
MISOA	VIIIA		VV.Z.Z			•		
Output voltage of logic "L" of	V_{OHA}			VIN		V		
MOSIA, /CSA, CLKA	- 5177					·		
SPI Current Specifications		T	T		ī			
The sink current of MISOB,	I _{SINKB}		18	30	52	mA		
ALARMB when output "L"	·ontre							
The source current of MISOB,	Isourceb	Isourceb	ISOURCEB		8	13	21	mA
ALARMB when output "H"	100011025		-					
The pull up resistor of MOSIB,	RPULLUP		0.9	1.75	2.6	kΩ		
/CSB, CLKB								
The sink current of MOSIA, /CSA,	Isinka		3	4	6	mA		
CLKA when output "L"								
SPI Timing Specifications		T	 		1			
MOSIB, MISOB valid to CLKB	t1 ⁵⁾		10			ns		
rising setup								
MOSIB, MISOB valid to CLKB	t2 ⁵⁾		250			ns		
rising hold								
CLKB low	t3 ⁵⁾		400			ns		
CLKB high	t4 ⁵⁾		400			ns		
/CSB rising edge to /CSB falling	t5 ⁵⁾	Normal mode	5					

edge		Low power mode	125			
CLKB rising edge to /CSB rising	t6 ⁵⁾	Normal mode	3			
edge	เชา	Low power mode	75			
/CSB falling edge to CLKB rising	t7 ⁵⁾	Normal mode	3			μs
edge	(<i>I</i> **)	Low power mode	75			
Stack Device Address Configuration	ion					
Threshold of logic "L" of SRN,						
SRP, ISP, ISN for device address					1.4	V
configuration						
Threshold of logic "H" of SRN,						
SRP, ISP, ISN for device address			3.2			V
configuration						
The pull up current of SRP to				44		
internal 5V	I _{SRP}			11		μΑ
The pull down resistor of ISP,	Raddress			200		kΩ
ISN, SRN	∧ ADDRESS			200		K77

Note:

5) Guaranteed by design.

TIMMING DIAGRAM



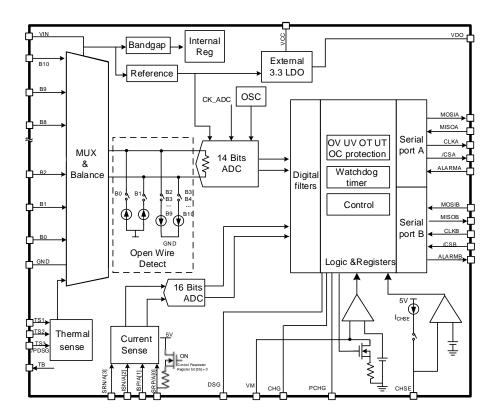
SPI Communication Timing Waveforms

PIN DESCRIPTION

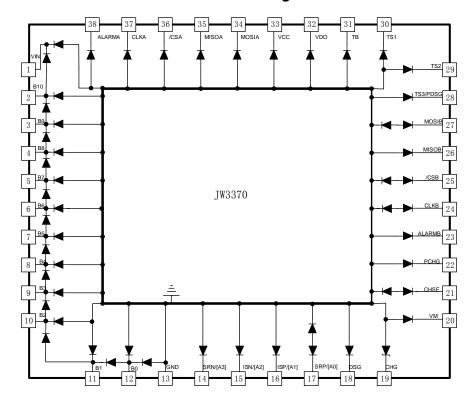
PIN No.	NAME	DESCRIPTION	
1	VIN	Maximum Voltage Input. The typical VIN is the same potential as B10.	
2	B10	Cell 10 +. Sense voltage for 10th cell positive terminal.	
3	В9	Cell 9 +. Sense voltage for 9th cell positive terminal.	
4	B8	Cell 8 +. Sense voltage for 8th cell positive terminal.	
5	В7	Cell 7 +. Sense voltage for 7th cell positive terminal.	
6	В6	Cell 6 +. Sense voltage for 6th cell positive terminal.	
7	B5	Cell 5 +. Sense voltage for 5th cell positive terminal.	
8	B4	Cell 4 +. Sense voltage for 4th cell positive terminal.	
9	В3	Cell 3 +. Sense voltage for 3rd cell positive terminal.	
10	B2	Cell 2 +. Sense voltage for 2nd cell positive terminal.	
11	B1	Cell 1 +. Sense voltage for 1st cell positive terminal.	
12	В0	Cell 1 Sense voltage for 1st cell negative terminal.	
13	GND	Ground	
		This is a dual-purpose pin.	
14	SRN/[A3]	Short detect Negative Input.	
		2) Device address configuration input for cascade application	
		This is a dual-purpose pin.	
15	ISN/[A2]	Negative Current Sense Input.	
		Device address configuration input for cascade application	
		This is a dual-purpose pin.	
16	ISP/[A1]	Positive Current Sense Input.	
		Device address configuration input for cascade application	
		This is a dual-purpose pin.	
17	SRP/[A0]	Short Detect Positive Input.	
		Device address configuration input for cascade application	
18	DSG	Discharge Switch Gate Driver.	
19	CHG	Charge Switch Gate Driver.	
20	VM	Pin for detecting load connection.	
21	CHSE	Pin for charger detection.	
22	PCHG	Pre-charge MOSFET Driver.	
23	ALARMB	Alarm Output. ALARMB send data to below unit or host processor in the	
20	/ LE II (IVI)	daisy chain.	
24	CLKB	Serial Clock Input. CLKB receive data from below unit or host processor	
	02.13	in the daisy chain. See serial port in the typical application section.	
		Chip Select Input (Active Low). /CSB receives data from below unit or	
25	/CSB	host processor in the daisy chain. See serial port in the typical application	
		section.	
26	MISOB	Serial Data Output. MISOB sends data to below unit or host processor in	
		the daisy chain. See serial port in the typical application section.	

27	MOSIB	Serial Data Input. MOSIB receives data from below unit or host processor
21	WOOD	in the daisy chain. See serial port in the typical application section.
		This is a dual-purpose pin.
28	TS3/PDSG	(1) Thermal Sensor Input 3. The details refer to the TS1 pin.
20	153/PD5G	(2) Pre-discharge MOSFET Driver
		Configuration by MCU
29	TS2	Thermal Sensor Input 2. The details refer to the TS1 pin.
		Thermal Sensor Input 1. A simple thermal resistance and resistor
		combination connected to the TB pin can be used to monitor
30	TS1	temperature. The ADC measures the voltage on TS1 pin and stores the
		result in the registers. Any voltage from 0V to 3.3V referenced to GND
		can be measured.
31	ТВ	Thermal bias 3.3V output.
00	1/00	3.3V LDO Output. This pin should be by passed with a 1µF capacitor.
32	VDO	The VDO pin is capable of supplying up to 50mA to an external load.
33	VCC	Input source for VDO, MOSFET driver and CHSE.
		Serial Data Output. The MOSIA pin is an NMOS open drain output, and
34	MOSIA	send data to the above unit in the daisy chain. See serial port in the
		typical application section.
0.5	MICOA	Serial Data Input. MISOA receives data from above unit in the daisy
35	MISOA	chain. See serial port in the typical application section.
		Chip Select Output (Active Low). The /CSA pin is an NMOS open drain
36	/CSA	output, and send data to the above unit in the daisy chain. See serial port
		in the typical application section.
		Serial Clock Output. The CLKA pin is an NMOS open drain output, and
37	CLKA	send data to the above unit in the daisy chain. See serial port in the
		typical application section.
20	A1 A D M A	Alarm Input. ALARMA receives data from above unit in the daisy chain.
38	ALARMA	See serial port in the typical application section.

BLOCK DIAGRAM



JW3370 Block Diagram



JW3370 Internal ESD Protection Structures

FUNCTIONAL DESCRIPTION

JW3370 is a monitor and protection IC capable of measuring the voltage, the temperature and current by an internal 14-bit $\Delta\Sigma$ ADC and 16-bit $\Delta\Sigma$ ADC, and integrates complete protection functions including over/under voltage, over/under temperature, over charge / discharge current, short and open wire. Two voltage ADC operation modes are provided to well satisfy multiple different application fields.

JW3370 has two built-in FET drivers, CHG and DSG, which controls NMOS FETs in the charge/discharge loop. Under alarm condition, the FETs could be set to response the alarm condition. Additionally, JW3370 provides passive balance for each battery cell. It is controlled by the host processor. The host processor writes values to configuration register inside the JW3370 to control the switches. And the balance could be disabled by the host processor.

JW3370 communicates with external control unit by a SPI serial interface. Two or more JW3370 can operate in series when the total voltage of battery stack is higher than 50V, or the total quantity of battery cells exceeds 10. JW3370 can pass the data up and down a stack of devices by the external resistor.

Over View of Operation Mode

JW3370 supports three modes of operation: Sleep, Ship, and Normal. Sleep mode is a power saving state where all circuits except the serial interface, LDO and driver are turned off. Ship mode is lowest possible power state, which only charger wakeup and /CSB wakeup circuit is enabled. Normal mode is the full operation state. The three modes key distinctions are shown in the below table.

Figure 1 shows three modes entry and exit conditions.

Normal	Sleep	Ship
Fully operation state. Voltage ADC is on. Over or under voltage protection, over temperature or under temperature is enabled. Current ADC is on and the over current protection and short protection is enabled. All the registers could be configured by host processor	Lower power state. Voltage ADC, current ADC and TB are all off. Mainly Serial Interface, LDO, Driver are on. And low current wakeup and charger wakeup function is active. Short circuit is on. In this state CHG and DSG enable registers can't be set on.	Lowest power state. All circuits are shutdown except charger wakeup and /CSB wakeup function is enabled.

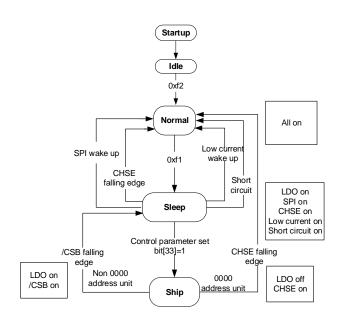


Figure 1. Operation Mode State Diagram

Ship Mode

When 0000 address unit enter ship mode, LDO off, CHSE on. Non 0000 address unit enter ship mode, LDO on, which is used for /CSB wake up.

Ship mode is the lowest power state, which can be used for shipping or long-term storage. For the lower power saving, it may be entry ship mode by the host command "power down Oxf1". When the device exits ship mode, it will boot and read parameters stored in register (if that has been written). If the register has not been written, the device will power up with default settings, and then settings can be changed by the host writing device registers.

It takes 1s delay to enter ship mode from sleep mode. Setting bit [40] of Control parameter set to "1" can shorten the time to enter ship mode to 1.28ms.

Charger Detection and Wakeup

Charger detection circuit is always on. When a falling edge is detected in CHSE pin, the IC enters to normal mode from ship mode. And the

ALARMB pin sends high signal to MCU. It's only applicable to address unit 0000.

/CSB Wakeup

/CSB wakeup function is always on. When a falling edge is detected in /CSB pin, the IC enters to sleep mode from ship mode. It's only applicable to non 0000 address unit.

Sleep Mode

JW3370 enters or exits Sleep Mode by "power down 0xf1" and "power wakeup 0xf2". In this mode, the CHG and DSG MOSFET status is keep as the previous states and the Low Current Wakeup function could be selected on. Once the charge / discharge current is over the Low Current Wakeup Threshold (V_{LC}) setup by "Current parameter set 0x08" [63-62] bit and this status remains for 30ms, JW3370 informs host processor and wakes up itself.

And the Low Current Wakeup operation can be disabled by host processor configuration registers.

Charger Detection and Wakeup

Charger detection circuit is always on. When a falling edge is detected in CHSE pin, the IC enters to normal mode from ship mode. And the ALARMB pin sends high signal to MCU and wakeup MCU.

SPI Wakeup

In the sleep mode, SPI circuit is on. MCU could send wakeup command to entry normal mode.

 Low Current Wakeup and Short Circuit Wakeup

In the sleep mode, when the low current or short current is detected, the IC enters to normal mode from sleep mode, and the ALARMB pin sends high signal to MCU.

Normal Mode

Normal mode represents the fully operation mode where all blocks are enabled and the device sees its highest current consumption.

JW3370 can monitor each cell voltages for over voltage and under voltage conditions. Internal 14-bit $\Delta\Sigma$ ADC enables high-accuracy measuring for battery voltage and temperature. Two 1k resistors and a 22nF capacitor are recommended to make up the front differential filtering network, which are enough for filtering transient voltage spikes. When the IC starts up, it's in sleep mode. And then enters normal mode through the MCU configuration. Figure 2 simply shows the MCU task.

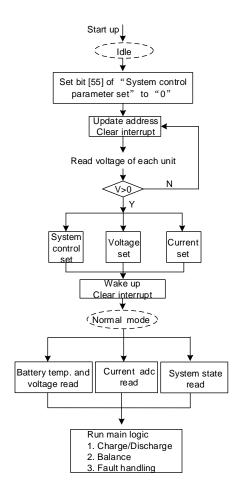


Figure 2. Task Handling Flow Chat

JW3370 can typically be used with as few as four cells, which is guaranteed by the low enough VIN start-up voltage. When JW3370 is used to monitor less than 10 cells, 8 cells for example, B0~B2 pins are all shorted and the above B2~B10 pins are connected to the monitored cells. The useful series battery numbers by "Control parameter set 0x0d" [3:0] bit. The unused inputs could result in a 0V reading for those channels. Figure 3 shows the example of JW3370 when used to monitor 8 cells.

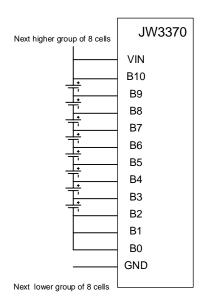


Figure 3. Monitoring 8 Cells with JW3370

In the normal case, the ADC senses the 10 voltage channels circularly, the 3 thermal channels are sensed after 10 times voltage sensing. The ADC can be commanded to measure any individual channel by host processor.

Considering the accuracy of ADC measurement, it is recommended to wait for 100ms delay before measures cell voltages and temperatures when waking from sleep mode to normal mode.

Monitor

The monitoring subsystem ensures that all cell voltages, temperatures, and pack current easily measured by the host. All ADCs are trimmed by Joulwatt.

JW3370 has a fully digital interface: All information is transferred through SPI, simply by reading or writing to the appropriate register(s) storing the relevant data. Block reads and writes, buffered by an 8-bit CRC code per byte, ensure a fast and robust transmission of data.

Cell Voltage Measurement

Each JW3370 measures cell voltages and temperatures using a 14-bit ADC. This ADC measures all differential cell voltages, thermistors with a nominal full-scale unsigned range of 0–5.0 V and LSB of 0.305mV.

The ADC is on automatically whenever the device enters normal mode. Once ADC is on and the protection thresholds are set, the integrated OV, UV, battery temperature and over current protections are functional.

Each cell measured time is about 0.64ms and a complete update is available every 6.4ms. The time can also be regulated by "Voltage parameter set 0x0E" [51:48] bit. (Register setting taking JW3370 address 0000 as example, for cascaded application only change JW3370 address).

The ADC transfer function is a linear equation defined as follows:

$$V_{CELL}(V) = ADC_{CELL} * GAIN$$

ADCCELL is the measurement results of each cell.

GAIN is fixed 0.305mV/LSB.

An example cell voltage calculation is provided in the table below. *The cell voltage can read* by "Voltage ADC Read 0x04" [207:48] bit.

14bit	ADC Result	GAIN	Cell
ADC Result	in Decimal	(mV/LSB).	Voltage(mV)
0x92e	2350	0.305	717

Note: Each differential cell input is factory-trimmed for gain and offset and requires no additional calibration or correction factor application, except for cell1, which requires an additional 2.5mV offset.

Cell Temperature Measurement

Cell temperature and voltage monitor use same ADC. To convert the thermistor resistance into temperature, please refer to the thermistor component manufacturer's datasheet.

Note: In JW3370 cascaded application, for Ts1~3 sampling, the /CSB should drive low for 103 VADC sampling cycles firstly, then send "Voltage ADC Read" command by MOSIB & CLKB and receive data and MISOB pin. And Ts value should add 18mV for offset compensation.

Pack Current Measurement

A 16bit integrating ADC, commonly referred to as the coulomb counter provides measurements of accumulated charge across the current sense resistor.

The current ADC is always on and the integration period for this reading is 132ms.

The full scale range of the CC is ± 190 mV, with a max recommended input range of ± 190 mV, thus yielding an LSB of approximately 6 μ V.

The following equation shows how to convert the 16-bit current ADC reading into an analog voltage:

$$V_{ISP-ISN}(mv) = ADC_{CURR} * GAIN - 200$$

ADC_{CURR} is the measurement results of current sense. GAIN is fixed 0.0061mV/LSB.

An example cell voltage calculation is provided in the table below. *The pack current can read by "Current ADC Read 0x07"* [15:0] bit.

16bit ADC	ADC Result	GAIN	VISP-ISN
Result	in Decimal	(mV/LSB).	(mV)
0x1e82	7810	0.0061	-152.33

Protection

Over/Under Voltage Protection

The JW3370 monitor each cell voltage. If one cell voltage is over the Over Voltage Threshold (V_{OVP}) or under the Under Voltage Threshold (V_{UVP}) and this status lasts for an adjustable delay time, JW3370 turns off charge MOSFET or discharge MOSFET and sends alarm signal to inform host processor.

If fewer than 10 cells are connected to the JW3370 then it is necessary to set the useful series battery numbers by configuration registers. If the number is set to 8, then the input for cells 1 and 2 are automatically masked.

The OVP and UVP threshold can set by "0x0e Voltage parameter set" CMD [31:24] and [23:16] bit, and OVP delay time can set by "0x0e Voltage parameter set" CMD [62], [60], [47:40] bit. Besides, the OVP and UVP flag can be accessed by "0xfb Alarm & Open-wire Info Get" [71:48] bit.

Over/Under Temperature Protection

JW3370 provides 3 temperature sensing PINs for detecting the temperature of battery cells. A NTC resistor is placed nearby battery cells. When the temperature of battery cells increases, the divided voltage input to TS pin is increases. Once the battery temperature is over the Over Temperature Threshold (Totp) or under the Under Temperature Threshold (Tutp) and this status lasts for an adjustable delay time, JW3370 turns off charge MOSFET or discharge

MOSFET and sends alarm signal to inform host processor. Sensors can be powered directly from TB as shown in Figure 4.

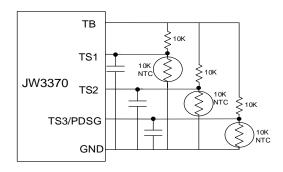


Figure 4. Driving Thermistors Directly from TB

If only one temperature sensing channel is used, it is strongly recommended to use the connection method shown in Figure 5.

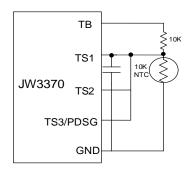


Figure 5. Single channel temperature sensing

The OTP and UTP and delay time can set by "voltage parameter set 0x0e" [79:64], [15:0], [39:32], and the OTP and UTP flag can read by "Detail Alarm Info Get 0x0b" [43:41], [39:37].

For charging process, the T_{OTP} / T_{UTP} is recommended to be set as 45°C / 0°C . For discharging process, the T_{OTP} is recommended to be set as 65°C or 75°C and the T_{UTP} - 10°C or - 20°C . The OTP / UTP delay time can be chosen from $0\sim7.68s$ (512ms step).

TS3/PDSG can be selected through register configuration. In Voltage parameter set, set bit

[59] to 1 to enable TS3 temperature sensing. The default power up of the IC is PDSG.

Charge Over Current Protection

If the battery current is over Charge Current Threshold (V_{COI}) and remains for a delay time, JW3370 shuts down the CHG and DSG.

The COI threshold and delay time can set by "Current parameter set 0x08" [15:8] and [59:56] bit, and COI flag can read by "Detail Alarm Info Get 0x0b" [35] bit.

Discharge Over Current Protection

If the battery current is over Discharge Current Threshold (V_{DOI}) and remains for a delay time, JW3370 shuts down the DSG.

The DOI threshold and delay time can set by "Current parameter set 0x08" [39:24] and [55:45] bit, and DOI flag can read by "Detail Alarm Info Get 0x0b" [32:31] bit.

Load Short Protection

If the voltage of external sense resistor (R_{sense}) is over Short Threshold (V_{OS}) and remains for a delay time, JW3370 shuts down the DSG.

The V_{OS} and the delay time can be setup by "Current parameter set 0x08" [74:70] and [68:64]. The delay time can be chosen from $0\sim2.048$ ms (64 μ s step). OS flag can read by "Detail Alarm Info Get 0x0b" [28] bit.

Cell Open Wire Detection

When a cell voltage sensing wire is open, the measurement results of the two cells close to the open cell are affected.

JW3370 provides two pull-down current sources for the open wire detection of B2 to B10 and two pull-up current sources for the open wire detection of B0 and B1. If a cell input pin is floating due to an open wire condition, this current discharges the capacitance, causing the

voltage at the pin to slowly drop. This drop in voltage eventually triggers a protection fault on that particular cell and the cell above it. Take B9 open connection for example, after several cycles of measuring battery cell9 and cell10, the current source is engaged, the potential at B9 is pulled down. The ADC reading for cell9 could approach zero and reading cell10 approach full scale. The measurement result of cell9 and cell10 different from the previous cycle measurement result over 200mV, the JW3370 will send open wire signal to host processor. MCU is needed in the open wire detection of B0 and B10 by monitoring the voltage of cell 1 and cell 10. The under voltage protection of cell 1 or cell 10 triggered after open wire detection equals to the open wire of B0 or B10.

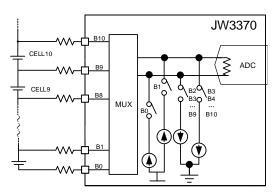


Figure 6. Open Connection

The Cell Open Wire Detection is executed by "Voltage parameter set 0x0e" [57:56] bit, and cell open wire flag can read by "Detail Alarm Info Get 0x0b" [27:17] bit. Periodic open wire detection is recommended.

Notes:

- 1. When the single cell voltage lower than 1.5V, the open-wire fault statue maybe submitted.
- 2. The B0 and B10 open-wire detection should be handled by MCU.
- 3. When open-wire fault happened will trigger over-voltage or under-voltage protection and turn off CHG or DSG MOSFET.

Control Subsystem

Charge/Discharge Switch MOSFET

JW3370 can drive two external N-MOSFETs to control the charge / discharge loop. When Charge Switch MOSFET (CHG) is shut down, the charge current of battery stack is cut off; and when Discharge Switch MOSFET (DSG) is shut down, the discharge current is cut off.

The CHG/DSG driving signal is set by "System control 0x02 ([23:21] bit set to 100)" [3:0] bit, and CHG/DSG FET status can read by "Detail Alarm Info Get 0x0b" [15:14] bit.

The CHG and DSG FET drivers can only be turned on when the JW3370 in Normal mode and there are no faults. Any protection parameters can be set in real-time, and if the protection is not triggered, the CHG and DSG FET drivers will remain turned on.

Figure 7 shows the CHG and DSG FET circuit. The highest driving voltage of CHG and DSG is 12V and the falling time of DSG is about 100ns with 95mA sinking current and 1nF load capacitor.

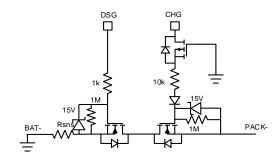


Figure 7. CHG and DSG FET Circuit

ALARM

The ALARMB pin serves as an active high digital interrupt signal that can be connected to a GPIO port of the host microcontroller. This signal is an OR of all bits in the system state register. Most of the states are fault events. The

faults and the FET state is shown in the table below.

System States	Interru pt	ALARM	Control	
	Inform		СНС	DSG
Charge mode: over				
voltage, over/under	Yes	Yes	OFF	ON
Temp				
Discharge mode:				
under voltage,				
over/under Temp,	Yes	Yes	ON	OFF
over current, short				
current				
Charge over				
current, ALARM pin	Yes	Yes	OFF	OFF
open wire				
Cell Open Wire	No	No	N	0
Balance ON/OFF	Yes	No	N	0
Load Present	Yes	No	No	
ТВ ОТР	Yes	Yes	No	
LDO OTP	Yes	Yes	No	
Low current wakeup	Yes	Yes	No	
charger wakeup	Yes	Yes	N	0

In order to clear the ALARMB signal, the source bit in the system state register must first be cleared by "clear interrupt flag" instruction.

Some fault event triggers automatic disabling of both CHG and DSG FET drivers. And recovery from a fault event must be handled by the host microcontroller.

In cascaded mode application, when there is no fault, the ALARB of non 0000 address chip sends out pulse signal with high level time of 4ms and cycle of 8s as the detection and judgment of alarm open wire enable. When a non 0000 address ship enter failure mode, its ALARMB sends out a pulse signal. There are three types of pulse signals correspond to three types of faults.

- 1. Pulse signal with high level time of 5-14ms and cycle of 100ms, turn off CHG FET.
- 2. Pulse signal with high level time of 15-25ms and cycle of 100ms, turn off DSG FET.
- 3. Pulse signal with high level time of 30-50ms and cycle of 100ms, turn off CHG FET and DSG FET.

The ALARMB State is shown in the Figure 8.

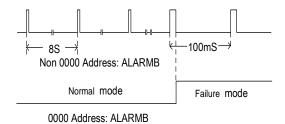


Figure 8. ALARMB State

Pre-Charge and Pre-Discharge Function

JW3370 integrated pre-charge and pre-discharge drivers for the deep discharge battery or some big capacitor load startup.

The pre-charge and pre-discharge FET driving signal is set by "System control 0x02 ([23:21] bit set to 100)" [9:8] bit. Pre-discharge function is not compatible with the thermal sensing function.

Passive Balance

JW3370 allows host processor choosing the battery cells to be discharged. When a cell is selected by "System control 0x02 ([23:21] bit set to 000)" [9:0] bit, an internal discharging MOSFET is turned on, which also turns on an external balancing Bipolar to largely increase the discharging current. An external resistor of 47Ω recommended to limit the power dissipated by the external Bipolar.

The balancing operation is turned off when any condition below is happening:

1.Communication with the host processor is interrupt for watchdog timer (t_{WD}) ;

- 2.Battery under voltage protection;
- 3. The temperature of JW3370 is beyond T_{BALAN}.

The balancing circuitry will not release after under voltage protection clear away. However, it's released if both of the following conditions are satisfied:

- 1.Resume communication with the host processor;
- 2. The temperature of JW3370 returns to T_{BALAN HYST} or even lower.

JW3370 allows at most 3 consecutive cells being discharged simultaneously. If host processor chooses 4 or more consecutive cells, the discharging switches of the lowest cell of each 4 cells will be prohibited turning on.

Considering the accuracy of ADC measurement, while a cell is being measured, the discharge switches for this cell and the cell above and below are all disabled. The harshest conditions are listed below when all cells discharge simultaneously.

Mode Cell	1	2	3	4	5	6	7	8	9	10
1	S	F	F	F	F	F	D	D	D	F
2	F	S	F	D	D	D	F	D	D	D
3	D	F	S	F	D	D	D	F	D	D
4	D	D	F	S	F	D	D	D	F	D
5	D	D	D	F	S	F	D	D	D	F
6	F	D	D	D	F	S	F	D	D	D
7	D	F	F	F	F	F	S	F	D	D
8	D	D	D	D	D	D	F	S	F	D
9	D	D	D	D	D	D	D	F	S	F
10	F	D	D	D	D	D	D	D	F	S

S-Sample: the cell is being measured

D-Discharge: internal discharging MOSFET is turned on

F-OFF: internal discharging MOSFET is turned off

The detailed circuit is shown in the Figure 9.

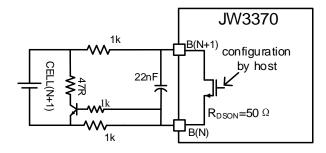


Figure 9. External Discharge Circuit Connection

(One cell)

The following equation shows how to calculate the balance current.

$$I_{BAL}(A) = MIN(\frac{V_{CELL}(V)}{R_{BAL}(\Omega)},\beta I_b) + \frac{V_{CELL}(V)}{R_{DSON}(\Omega) + 1k\Omega + 1k\Omega}$$

Load State Detection

The VM pin is for load state detection. The comparison result of VM voltage and V_{VM} is used as a condition of interrupt releasing. In the normal status, the internal resistance (R_{VMS}) between the VM pin and GND pin are not connected. When the over-discharge or discharge over current status occurs, MCU sends commend to enable load detection circuit. R_{VMS} are connected until the status is released.

When load detection function is enabled by [5] bit of "System control 0x02 ([23-21] bit set 100)", the DECT pin output "H" logic. And the VM detection result can read by "Detail Alarm Info Get 0x0b" [10] bit.

Charger Detection

The CHSE pin is for charger detection. The comparison result of CHSE voltage and V_{CHSE} is

used as a condition of interrupt releasing. In the any status, the pin source I_{CHSE} for charger detection. The charger detection result can be accessed by "Detail Alarm Info Get 0x0b" [2] bit.

If the CHSE voltage is lower than V_{CHSE} , it is considered that the charger is plugged in. Otherwise, it is considered that the charger is removed.

Note: If the charger detection function is not required in practical applications, the CHSE pin should be no connection.

LDO

JW3370 provides 3.3V LDO for external application. The current limitation of LDO output is 100mA.

JW3370 provides two-step over-temperature protection for LDO. When the temperature detected reaches 125°C, JW3370 could warn host processor. If the temperature exceeds 150°C, LDO could be shut down.

Power

LDO/driver module power supply is VCC. PCHG/PDSG/CHSE pull-up, power supply is VCC, others power supply is VIN.

SPI Communication

JW3370 provides two groups of SPI data interface. MISOB is used for sending data to lower unit or host processor; MOSIB, /CSB and CLKB are used for receiving data from lower unit or host processor; MISOA is used for receiving data from upper unit; MOSIA, /CSA and CLKA are used for sending data to upper unit. A 1k resistor must be connected in series between communication pins of the cascade units. Also, external pull-up for MOSIB, /CSB, CLKB through a 10k resistor and a 5V zener is connected in parallel. It is used for updating

address while the cascade unit communication loss occurred. When this happens, the baud rate needs to be reduced to 1 / 10 of the original.

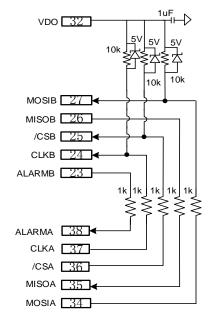


Figure 10. SPI Communication in Cascade

Application

Host processor writes values to configuration registers inside JW3370 to setup the protection thresholds, delay time and control switches, which facilitates users to make settings and choose operating mode freely. The watchdog timer on the JW3370 will turn off the balancing circuitry if communication with the host processor is interrupt for watchdog timer (twD, 0~2min, 512ms step). The balancing circuitry will release when any command setup is successful.

Clock Phase and Polarity: JW3370 SPI compatible interface is configured to operate in a system using CPHA=1 and CPOL=1. Consequently, data on MOSIB must be stable during the rising edge of CLKB and while stop communication, MCU needs to pull high the input pins MOSIB, CLKB and /CSB.

Data Transfers: Every byte consists of 8 bits. On a write, the data value on MOSIB is latched into the device on the rising edge of CLKB (Figure11). Similarly, on a read, the data value output on MISOB is valid during the rising edge of CLKB. /CSB must remain low for the entire duration of a command sequence, including between a command byte and subsequent data.

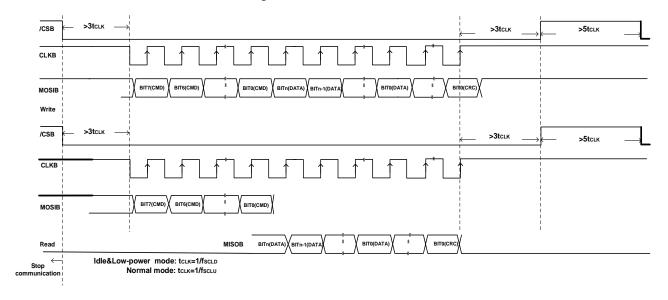


Figure 11. Transmission Format

Random Cell Connection Support

The JW3370 device supports a random connection sequence of cells to the device during pack manufacturing unless the battery negative terminal connected to Power GND of the JW3370 device first.

For example, cell-8 in a 10-cell stack might be first connected at the input terminals leading to pins B8 and B7, then cell-4 may next be connected at the input terminals leading to pins B4 and B3, and so on. It is not necessary to connect the negative terminal of cell-1 first at B0. As another example, consider a battery stack that is already assembled and cells already interconnected to each other, then the stack is connected to the PCB through a connector, which is plugged or soldered to the PCB. In this case, the sequence order in which the connections are made to the PCB can be random in time, they do not need to be controlled in a certain sequence.

Cascade Configuration

JW3370 supports cascade application. Several devices can be daisy chained in series.

Configure device address by the logic levels on the SRN/[A3], ISN/[A2], ISP/[A1], SRP/[A0] pins, as shown in below table.

SRN /[A3]	ISN /[A2]	ISP /[A1]	SRP /[A0]	Device Address
0	0	0	0	1
0	0	0	1	2
0	0	1	0	3
0	0	1	1	4
0	1	0	0	5
0	1	0	1	6
0	1	1	0	7
0	1	1	1	8
1	0	0	0	9
1	0	0	1	10

1	0	1	0	11
1	0	1	1	12
1	1	0	0	13
1	1	0	1	14
1	1	1	0	15
1	1	1	1	Broadcast

Note:

6) SRP/[A0] is pull up to the 5V by default. The updating address instruction must be written while SRP/[A0] is pull up to the 5V. So update the address first after power on, voltage measured of all cascade units is greater than 0 indicates the address is correct, then remove the internal pull up by set control parameter register bit [55] to 1. This bit set to 1 will remove the function of updating address, and enable ADC, small current wake up and ship mode entry.

SPI Power Consumption in Cascade Application

The power consumption of SPI communication occurs when /CSB, MOSIB and CLKB pins are pulled down and MISOB pin is pulled up. The maximum power consumption can be estimated as the sum of sampling power consumption of voltage and current.

$$I_{u} = I_{SINKA} * 28 * 8 * \frac{\left(1 + 0.5 + \frac{I_{SOURCEB}}{I_{SINKA}} * 0.5\right)}{f_{clku} * T_{sample-v}}$$

$$I_i = I_{SINKA} * 5 * 8 * \frac{\left(1 + 0.5 + \frac{I_{SOURCEB}}{I_{SINKA}} * 0.5\right)}{f_{clku} * T_{sample-i}}$$

The recommended sampling period:

 $T_{sample-v}$ =500ms.

The recommended sampling period:

 $T_{sample-i}$ =200ms.

PCB Layout Precaution

The PCB layout of JW3370 must be carefully designed.

- The TB and VDO pins should be bypassed with a 0.1μF and 1μF capacitor respectively.
- Care should be taken when placing the ADC input filter capacitors to minimize PCB trace impedances.
- 3) The quality of the Kelvin connections at the sense resistor is critical. The sense resistor must have a temperature coefficient no greater than 50 ppm in order to minimize current measurement drift with temperature. Choose the value of the sense resistor to correspond to the available overcurrent and short circuit ranges of the JW3370 device.

- Parallel resistors can be used as long as good Kelvin sensing is ensured.
- 4) The JW3370 device uses an integrating delta-sigma ADC for current measurements. For best performance, 100Ω resistors should be included from the sense resistor terminals to the SRP and SRN inputs of the device, with a 10nF filter capacitor placed across the SRP and SRN pins. All filter components should be placed as close as possible to the device, rather than close to the sense resistor, and the traces from the sense resistor routed in parallel to the filter circuit. A ground plane can also be included around the filter network to add additional noise immunity.

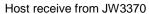
THE DETAILS FOR HOST PROCESSOR COMMAND REGISTERS

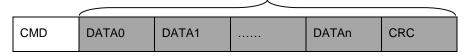
Instruction Structure

Write:

|--|

Read:





Note:

1. The command is effective, when "DATA0+DATA1+...+DATAn+CRC=0xff" is setup.

CMD Structure

Note:

- 1. A[3:0]: Configure the address to determine the useful IC except "A[3:0]≠1111". If "A[3:0]=1111" is set, the command is effective to all the stacked devices (Broadcast State).
- 2. C[2:0]: Commands set. Reference table 1 for the detail.
- 3. ODD: Odd check bit, ^{A[3:0], C[2:0], ODD}=1.

Table 1. CMD Instructions

C[2:0]	B/S	Function R/W		Data description
000	В	Power down W		All chips into sleep mode
000	S	Clear interrupt flag	W	Clear the interrupt fault flag bit set to 1 due to various faults
	В	Power wake up W		All chips into normal mode
001	s	Balance set	W	Set battery balancing related registers
	3	Alarm set	W	Set alarm related registers
	В	Set state to charge	W	Effective to all stacked units except the bottom one
010 S	Voltage ADC read	R	Read 14 bit data of 10 battery voltages and 3 battery	
			temperatures	
011	В	Set state to discharge	W	Effective to all stacked units except the bottom one
011	S	Current ADC read R		Read 16bit data of current
				Through {SRN,SRP,ISN,ISP} configure device address
	В	Update device address	W	*The device address updates when the IC is power-on or the
100			command is active	
	S	Current parameter set	R	Set charge discharge over-current threshold ,short-circuit
	S Current parameter set		IX.	protection threshold , delay time and small current detection

			threshold
В	Alarm & Cell open-wire info get	R	Read the alarm and battery status of all cascaded chips
S	Detail alarm info get	R	Read the detailed fault interrupt flag bit of a chip
B/S	Control parameter set	W	Set control related registers
B/S	Voltage parameter set	R	Set the over / under voltage (temperature) threshold and delay time
	S B/S	B info get S Detail alarm info get B/S Control parameter set	B info get R S Detail alarm info get R B/S Control parameter set W

Note:

B: Broadcast command: A broadcast command is one to which all devices on the bus will respond, regardless of device address.

S: Sing command: effective to specified device.

R: read. W: write.

Table 2. Single Byte Instructions

Item	Content	Description
Power Down	0xf1	
Power Wakeup	0xf2	
Set state to charge	0xf4	
Set state to discharge	0xf7	
Update device address	0xf8	the command is effective when bit [55] of "System control
		parameter set" is set to "0"
Clear interrupt flag	xxxx_000x	0x01, 10, 20, 31, 40, 50, 51,
		0x01: unit1;
		0x20: unit2 of the cascade;
		0x31: unit3 of the cascade;

Table 3. Alarm & Open-wire Info Get

Item	Content	Description
CMD(1B)		0xfb
DATA(4B)	[31:16]	Read ALARM interrupt flag of 16 stacked devices
DATA(4b)	[15:0]	Read cell open wire flag of 16 stacked devices

Table 4. Detail Alarm Info. Get

Item	Content	Description
		0x0b, 0x1a, 0x2a, 0x3b
		0x0b: unit1;
CMD(1B)		0x1a: unit2 of the cascade;
		0x3b: unit3 of the cascade;
DATA(9B)	[71:62]	Read over voltage interrupt flag of 10 cells, bit [71] corresponds

		to the 10th bettery			
	[04,50]	to the 10th battery			
	[61:58]	Reserved			
	[57:48]	Read under voltage interrupt flag of 10 cells, bit [57] corresponds			
	[47.44]	to the 10th battery			
	[47:44]	Reserved			
		Read over temperature interrupt flag of 3 channels			
	[43:41]	bit [41]: TS1 over temperature			
		bit [42]: TS2 over temperature			
		bit [43]: TS3 over temperature			
	[40]	Reserved			
		Read under temperature interrupt flag of 3 channels			
	[39:37]	bit [37]: TS1 over temperature			
	[00.07]	bit [38]: TS2 over temperature			
		bit [39]: TS3 over temperature			
	[36]	Reserved			
	[35]	Read over current interrupt flag in charge state			
	[34]	Turn off DSG FET for upper chip instruction			
	[33]	Turn off CHG FET for upper chip instruction			
	[32:31]	Read over current interrupt flag in discharge state, bit [32]			
		correspond to two grades protection			
	[30]	Reserved			
	[29]	Reserved			
	[28]	Read short circuit interrupt flag in discharge state			
	[07.40]	Read open wire interrupt flag, which corresponds to 10 cells,			
	[27:18]	bit[27] corresponds to the 10th battery.			
	[47]	Open wire detection completion flag indicates the bit, which can			
	[17]	be cleared only when the open wire detection enable is turned off			
		Wake up event flag bit except wake up sleep state with			
	[16]	command			
	[15]	Read the status of DSG FET			
	[14]	Read the status of CHG FET			
	[13]	Read over temperature interrupt flag of 3.3V TB subsystem			
	[12]	Read over temperature interrupt flag of 3.3V LDO subsystem			
	[11]	Read over temperature interrupt flag of balance subsystem			
		Read the status of VM pin.			
	[10]	0: Load connected 1: Load removed			
	[9]	Read stacked devices open wire interrupt			
	[8]	Reserved			
	[7]	Reserved			
	r. 1	Read the status of balance on-off. If the balance is disabled, the			
	[6]	bit [6] is "1", else, the bit [6] is "0".			
	[5]	Battery charge and discharge state, if bit [5] is 1, it is charged			
	ادا	Dattory orlange and disoriarge state, it bit [3] is 1, it is orlanged			

	[4]	When the chip sleep status indicator bit [4] is 1, the chip is in sleep state
	[3]	Reserved
	[2]	The chip detects the result indicator bit of charger comparator If the charger is removed, bit [2] is 1
	[1:0]	Reserved
CRC(1B)		\sum (DATA,CRC) = 0xff

Table 5. Voltage ADC Read

Item	Content	Description			
CMD(1B)		0x04, 0x15, 0x25, 0x34			
	B25B24	The ADC measurement results of cells 1			
	623624	{B25[5:0],B24[7:0]}→cell1			
		The ADC measurement results of cells 2 and 3			
	B23B22B21B20	{B23[5:0],B22[7:0]}→cell2			
		{B21[5:0],B20[7:0]}→cell3			
DATA(26D)	B19B18B17B16	The ADC measurement results of cells 4 and 5			
DATA(26B)	B15 B14B13B12	The ADC measurement results of cells 6 and 7			
	B11B10B9B8	The ADC measurement results of cells 8 and 9			
	DZDODED 4	The ADC measurement results of cells 10 and battery			
	B7B6B5B4	temperature channel 1			
	DODODADO	The ADC measurement results of battery temperature channel 2			
	B3B2B1B0	and 3			
CRC(1B)		\sum (DATA,CRC) = 0xff			

Table 6. Current ADC Read

Item	Content	Description			
CMD(1B)		0x07, 0x16, 0x26, 0x37			
	[23]	Current parameter set OK flag			
	[22]	Voltage parameter set OK flag			
DATA(OD)	[21]	Control parameter set OK flag			
DATA(3B)	[20]	Balance/Test/Alarm/Trim set OK flag			
	[19:16]	Reserved			
	[15:0]	The ADC measurement result of charge/discharge current			
CRC(1B)		Σ (DATA,CRC) = 0xff			

Table 7. Balance/ Alarm/ System Control Set

Item	Content			Default	Recommended	Description	
CMD(1B)	xxxx_001x			Delault	Recommended	0x02, 0x13, 0x23, 0x32	
DATA(3B)	[23:21] 000 [20:10]			0x0	0x0	Reserved	

	Balance set				Selection of cell for balancing
	Dalatice set				bit[0]→cell 1,bit[9]→cell 10
					1: cell balance selected
					0: cell balance not selected
		[9:0]	0x0	0x0	At most three consecutive batteries
					are allowed to discharge
					simultaneously. When ADC samples
					a certain battery voltage, the battery
					voltage and its upper and lower
					batteries do not discharge
		[20:13]	0x0	0x0	Reserved
		[12]	0x0	0x0	Force to 0
					Alarm open wire detection:
					1: alarm open wire detection is invalid
	010				0: under normal state, the cycle of
	Alarm set	[11]	0x1	0x1	Alarmb is 8s, and the pulse width of
					high level is 4ms. If the low level of
					Alarma lasting more than 16s(MAX) is
					detected, the line is open
		[10:0]	0x0	0x0	Reserved
		[20:16]	0x0	0x0	Reserved
		[45]	0.0	0.0	Analog module charger detection
		[15]	0x0	0x0	0: enable 1: disable
			0x0	0x0	Analog module short circuit
		[14]			comparator
					0: enable 1: disable
		[13]	0x0	0x0	Small current detection
					0: enable 1: disable
					Analog module chip address control
		[12]	0x0	0x0	0: enable 1: disable
		[11:10]	0x0	0x0	Reserved
	100				PDSG output control (works when
	System control				Ts3 temperature protection is
		[9]	0x0	0x0	disabled)
					0: output 0V
					1: output 5V
					PCHG output control
		[8]	0x0	0x0	0: output 0V 1: output 5V
		[7]	0x0	0x0	Reserved
		1.3			Setting of pull-up current during
		[6]	0x0	0x0	charger detection
		رقا	0,0		0: 1µA 1: 0.5µA
		[5]	0x0	0x0	VM load detection module enable
		[5]	UXU	UXU	vivi load detection module enable

					control
					0: disable
					1: enable
		[4]	0x0	0x0	Reserved
		[2]	0x0	0x0	Enable CHG
		[3]	UXU	UXU	0:disable 1:enable
		[2]	0x0	0x0	CHG status
					0:low,0V 1:high,12V
					* the command is effective when bit
					[3] is set to "1"
		[1]	0x0	0x0	Enable DISCHG
					0:disable 1:enable
					DISCHG status
		[0]	0.40	0.40	0:low,0V 1:high,12V
		[0]	0x0	0x0	* the command is effective when bit
					[1] is set to "1"
CRC(1B)					Σ (DATA,CRC) = 0xff

Table 8. Control Parameter Set

Item	Content	Default	Recommended	Description			
CMD(1B)				Broadcast: 0xfd; Single: 0x0d, 0x1c, 0x2c, 0x3d			
	[63]	0x0 0x0		Forced to 0			
	[62:58]	0x0	0x0	Reserved			
				Send control bit of alarm pin to close the CO / DO tube function			
	[57]	0x0	0x0	0: allow alarm pin to turn off the sending of CO / DO.			
				1: Disable alarm pin from sending CO / DO.			
				Detect the control bit of alarm pin closing CO / DO tube function			
	[56]	0x0	0x0	0: allow alarm pin to turn off CO / DO detection.			
	[56]	UXU	OXO	1: Disable alarm pin to turn off CO / DO detection, and clear the			
				corresponding status detection bit.			
		55] 0x0	0x1	0: Update address, update the address first after power on, voltage			
DATA(8B)				measured of all cascade units is greater than 0 indicates the address			
	[55]			is correct.			
				1: Forced to 1 after updating address successful, because only when			
				this bit is 1, the voltage ADC measurement can work normally			
	[54:52]	0x2	0x2	Forced to 2			
	[51:49]	0x2	0x2	Forced to 2			
	[48:46] 0x0 0x0		0x0	Forced to 0			
	[45:44]	0x2	0x2	Forced to 2			
				SPI /CSB wake up ship state			
	[43]	0x0	0x0	0: /CSB is low and cannot wake up;			
				1: /CSB is low and can wake up, enter sleep state;			

	[42:41]	0x0	0x0	Forced to 0
	[40]	0.0	0.0	Delay time to enter ship mode from sleep mode
	[40]	0x0	0x0	0: 1s 1: 1.28ms
	100 001			Chip cascade number: [39:36]+1
	[39:36]	0x0	User-defined	The default value is 0, single chip works
				Enable 3.3V TB operation
	[35]	0x0	0x0	0: enable(Recommended)
				1: disable
				Enable 3.3V LDO operation
	[34]	0x0	0x0	0: enable (Recommended)
				1: disable
	[22]	0,40	0.0	0: It is forbidden to enter ship mode in sleep mode
	[33]	0x0	0x0	1: ship mode is allowed in sleep mode
	[32]	0x0	0x0	Forced to 0
				Set the watchdog time(twD) of SPI communication; when no SPI
	[24.24]	0x78	0.79	communication state lasts for [31:24] * 512ms, if the balancing is on,
	[31:24]	UX/O	0x78	the balancing will be turned off; if any SPI instruction is sent, it will
				recover
	[23:22]	0x0	0x0	Forced to 0
				Poll Voltage ADC converter control
	[21]	0x0	0x0	0: poll status
				1: appointed ADC only
				Select respective cell measurement (from cell1 to cell10, TP1 to
				TP3)
	[20:16]	0x0	x0 0x0	0x00→cell1, 0x01→cell2,, 0x09→cell10
				0x0E→TP1, 0x0F→TP2, 0x11→TP3
				* respective cell voltage ADC measured data with bit [21] set to 1
	[15:12]	0x1	0x1	Forced to 1
				In sleep mode and the digital system clock is turn off, whether to turn
				on SPI communication timeout detection
	[11]	0x0	0x0	0: disable SPI communication timeout detection, but the
				communication flag will not be cleared
				1: Allow SPI communication timeout detection
	[10:7]	0x0	0x3	Forced to 3
	[6:4]	0x7	0x7	Forced to 7
	[3:0]	0x9	User-defined	Set the number of batteries =[3:0]+1
CRC(1B)				$\Sigma(DATA,CRC) = 0xff$

Table 9. Voltage Parameter Set

Item	Content	Default	Recommended	Description	
CMD(1B)				Broadcast: 0xfe; Single: 0x0e, 0x1f, 0x2f, 0x3e	
DATA(10B)	[79:72]	0xff	User-defined	Setting discharge under temperature protection threshold:	

			ı				
			([79:72]+1)*64*5/16384				
[71:64]	0x0	User-defined	Setting discharge ov	Setting discharge over temperature protection threshold:			
[71.04]	OXO	Osci delined	([79:72]+1)*64*5/163	384			
[63]	0x0	0x0	Reserved				
[62]	0x0	0.40	Time step of overvo	tage protection:			
	UXU	0x0	0 : 128ms	1 : 512ms			
[61]	0x0	0x0	Reserved				
[00]	00	00	Time step of under v	oltage protection:			
[60]	0x0	0x0	0 : 512ms	1:1024ms			
[50]	00	00	0: TS3 is forbidden t	o detect over and un	der temperature.		
[59]	0x0	0x0	1: TS3 is allowed to	detect over and unde	er temperature.		
[58]	0x0	0x1	Forced to 1				
[57]	0x0	0x0	Forced to 0				
			Open wire detection	enable of voltage AD	DC sampling line		
			0: the open wire de	tection function is dis	sabled;		
[56]	0x0	0x0	1: the open wire de	tection function is en	abled		
			-	detection must disabl			
[55:54]	0x0	0x0	Forced to 0				
[53:52]	0x1	0x1	Forced to 1				
			Voltage ADC measu	rement mode			
			0: fast mode (Recommended)				
			1: filtering mode				
[51]	0x0	0x0	* The processing time of fast mode is determined by bit[50:48]				
			setting				
			The processing time of filtering mode is 65ms				
			Voltage ADC measu				
[50]	0x1	0x1	1: The processing time is determined by bit[49:48] setting				
-				me of "simple count"			
			Setting waiting and	sampling time			
			[49:48]	waiting time	sampling time		
			00	128µS	512µS		
[49:48]	0x0	User-defined	01	256µS	512µS		
			10	256µS	1024µS		
			11	1024µS	1024µS		
			 				
[47:44]	0xf	User-defined	Over voltage protection delay time: Bit[62] =0, [47:44]*128ms;				
[]	07.1		Bit[62] =1, [47:44]*5				
			Under voltage prote				
[43:40]	0xf	User-defined	Bit[60] =0, [43:40]*	-			
[43.40]	UXI	Oser-delined	Bit[60] =1, [43:40]*				
[39:36]	0xf	User-defined	 	orotection delay time:	[39·36]*512me		
[35:32]	0xf	User-defined		<u> </u>			
[33.32]	UAI	USET-UEIITIEU	Over temperature protection delay time: [35:32]*512ms				

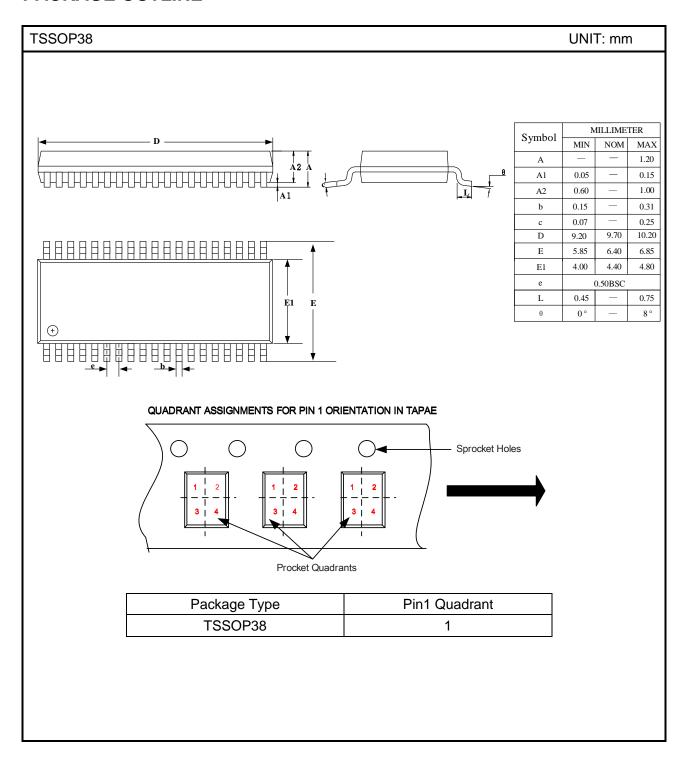
	[31:24]	0xff	User-defined	Over voltage threshold: ([31:24]+1)*64*5/16384V
	[23:16]	0x0	User-defined	Under voltage threshold: ([23:16]+1)*64*5/16384V
	[15:8]	0xff	User-defined	Setting charge under temperature protection threshold:
				([15:8]+1)*64*5/16384V
	[7:0]	0x0	User-defined	Setting charge over temperature protection threshold:
				([7:0]+1)*64*5/16384V
CRC(1B)				\sum (DATA,CRC) = 0xff

Table 10. Current Parameter Set

Item	Content	Default	Recommend	Description
CMD(1B)				0x08
	[79:76]		0x7	Charge/Discharge status detection threshold:
		0x7		±[79:76]*32*0.2/65536
				Default: 0.6836mV
				Charge status:
				V _{ISP-ISN} < - [79:76]*32*0.2/65536
				Discharge status:
				V ISP-ISN>[79:76]*32*0.2/65536
		0x5	User-defined	Short circuit threshold in discharge:
				{[75] *240mV+(~[74]) *120mV+(~[73]) *60mV+
				(~[72]) *30mV+(~[71]) *15mV+(~[70]) *7.5mV+42.5mV}
				Default: 237.5mV
	[75:70]			Hysteresis: 5mV
	[75.70]			Note: "~" is negation symbol, bit [74:70] need negation
				operation, for example, bit [75:70] set as 000101, the
				short circuit threshold is:
DATA (40D)				0*240mV+1*120mV+1*60mV+0*30mV+1*15mV+
DATA(10B)				0*7.5mV+42.5mV=237.5mV
	[69]	0x0	0x1	Forced to 1
	[68:64]	0x1f	0x1f	Short circuit delay time in discharge: ([68:64]+1)*64us
	[63:62]	0x2	0x2	Low current wakeup threshold (V _{LC}):
				0x2:350uV 0x3:400uV
				V _{SRP-SRN} within that range: the Sleep entry is permitted.
				V _{SRP-SRN} beyond that range: the Sleep entry is prohibited.
				Note: Only low current wakeup function is enabled
	[61:60]	0x0	0x0	Forced to 0
	[59:56]	0xf	User-defined	charge over current protection delay time; [59:56]*64ms
	[55:51]	0x1f	User-defined	The second grade over current protection delay time:
				[55:51]*step, Step is controlled by [45].
	[50:46]	0x1f	User-defined	The first grade over current protection delay time:
				[50:46]*256ms+128ms
	[45]	0x0	0x1	time step for secondary discharge over current protection
				0 : 4ms 1 : 32ms

	[44:40]	0x0	0xff	Reserved
	[39:32]	0xff	User-defined	The second grade over current protection threshold
		UXII		voltage in discharge:[39:32]*0.4/512
	[31:24]	0xff	User-defined	The first grade over current protection threshold voltage
		UXII		in discharge:[31:24]*0.4/512
	[23:16]	0x0	Oxff	Reserved
	[15:8]	0xff	User-defined	The over current protection threshold voltage in charge:
				-[15:8]*0.4/512
	[7:0]	0x0	0xff	Reserved
CRC(1B)				\sum (DATA,CRC) = 0xff

PACKAGE OUTLINE



IMPORTANT NOTICE

 Joulwatt Technology Co.,Ltd reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein.

- Any unauthorized redistribution or copy of this document for any purpose is strictly forbidden.
- Joulwatt Technology Co.,Ltd does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
- JOULWATT TECHNOLOGY CO.,LTD PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, SAFETY INFORMATION AND OTHER RESOURCES, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

Copyright © 2020 JoulWatt

All rights are reserved by Joulwatt Technology Co., Ltd.